

## FDBL86062-F085-VB Datasheet N-Channel 100 V (D-S) MOSFET

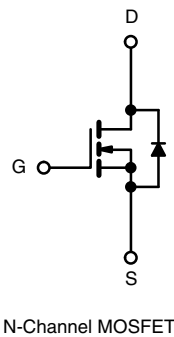
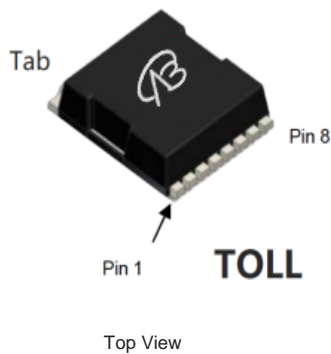
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)
100	0.002at V <sub>GS</sub> = 10 V	200	74 nC

### FEATURES

- SGT technology Power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>g</sub> and UIS tested



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**



### APPLICATIONS

- Power supplies:
  - Uninterruptible power supplies
  - AC/DC switch-mode power supplies
  - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Solar micro inverter
- Class D audio amplifier

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	100	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	200	A
	T <sub>C</sub> = 70 °C		120	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	600	
Avalanche Current	L = 0.5 mH	I <sub>AS</sub>	75	
Single Avalanche Energy <sup>a</sup>		E <sub>AS</sub>	1500	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	370 <sup>b</sup>	W
	T <sub>C</sub> = 100 °C		180 <sup>b</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>c</sup>		R <sub>thJA</sub>	40	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	0.4	

### Notes

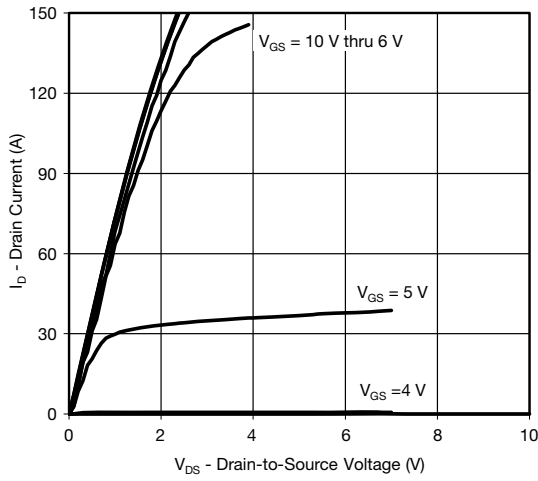
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR4 material).

SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	-	4.5	
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V	-	-	± 250	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	μA
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	150	
		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	90	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A	-	0.002	-	Ω
		V <sub>GS</sub> = 7.5 V, I <sub>D</sub> = 65 A	-	0.075	-	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A	-	75	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 100 V, f = 1 MHz	-	9600	-	pF
Output Capacitance	C <sub>OSS</sub>		-	246	-	
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	21	-	
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 60 A	-	74	96	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		-	16.7	-	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	16.9	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.5	3	5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	V <sub>DD</sub> = 100 V, R <sub>L</sub> = 1.66 Ω I <sub>D</sub> ≅ 60 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	15	29	ns
Rise Time <sup>c</sup>	t <sub>r</sub>		-	115	210	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		-	30	70	
Fall Time <sup>c</sup>	t <sub>f</sub>		-	80	150	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T<sub>C</sub> = 25 °C)</b>						
Pulsed Current (t = 100 μs)	I <sub>SM</sub>		-	-	600	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.8	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 30 A, di/dt = 100 A/μs	-	240	480	ns
Peak Reverse Recovery Charge	I <sub>RM(REC)</sub>		-	11	20	A
Reverse Recovery Charge	Q <sub>rr</sub>		-	0.9	1.8	μC

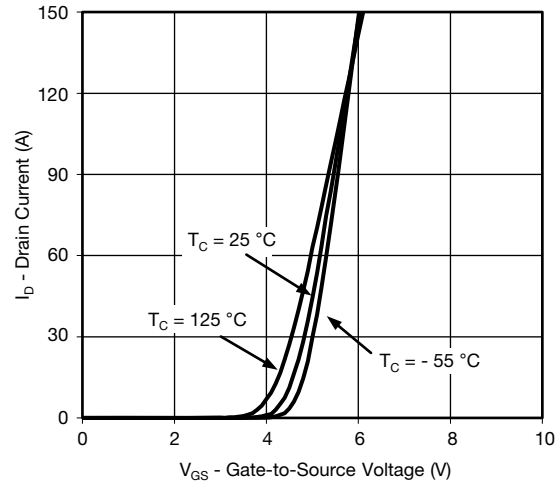
**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

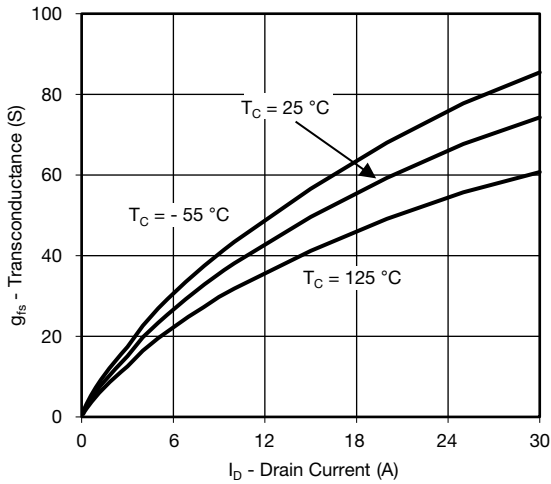
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



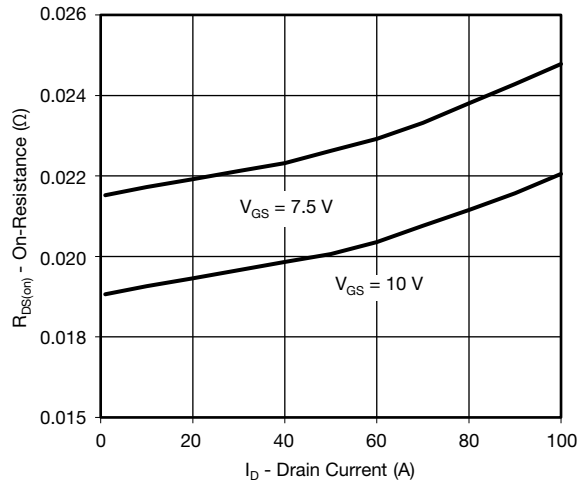
**Output Characteristics**



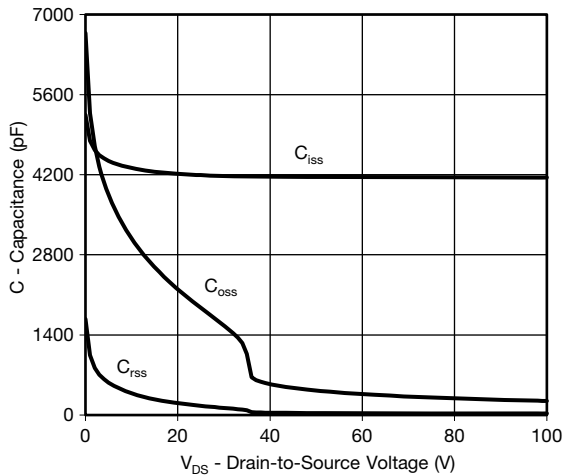
**Transfer Characteristics**



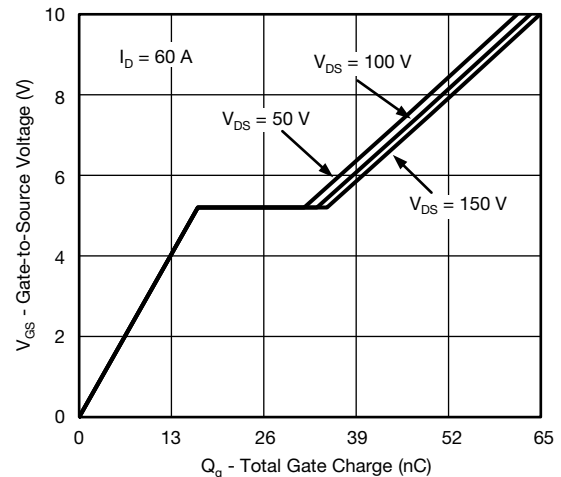
**Transconductance**



**On-Resistance vs. Drain Current**



**Capacitance**

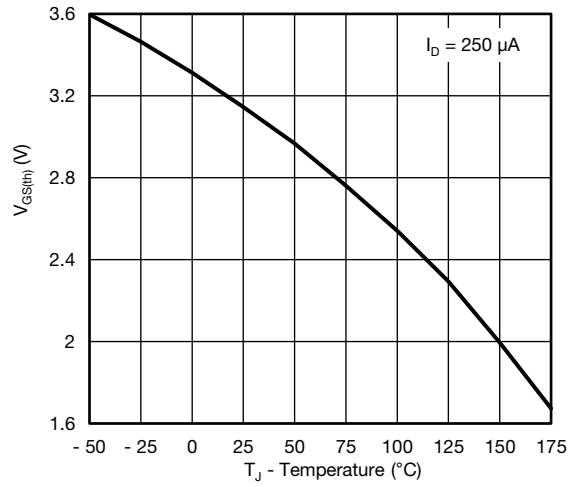


**Gate Charge**

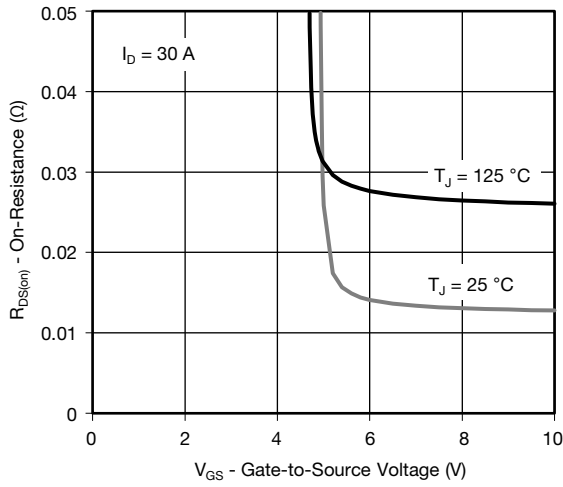
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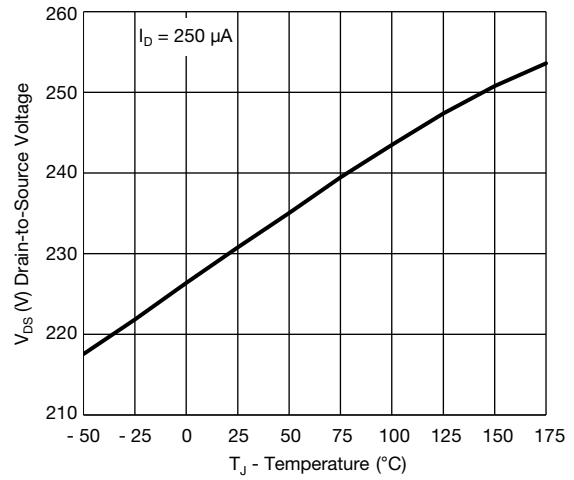
**On-Resistance vs. Junction Temperature**



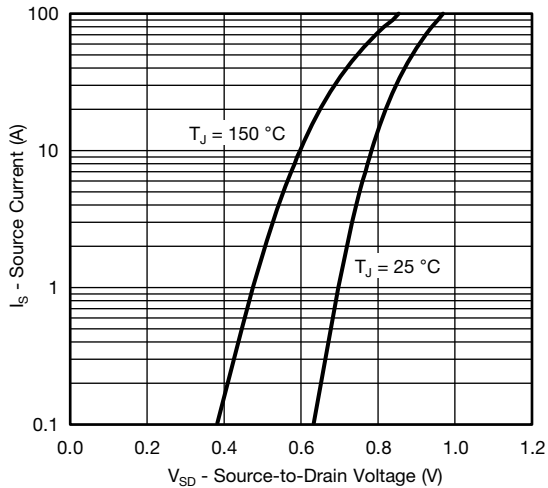
**Threshold Voltage**



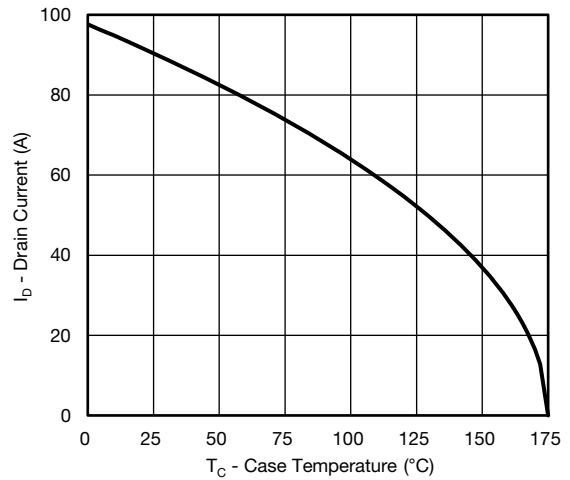
**On-Resistance vs. Gate-to-Source Voltage**



**Drain Source Breakdown vs. Junction Temperature**

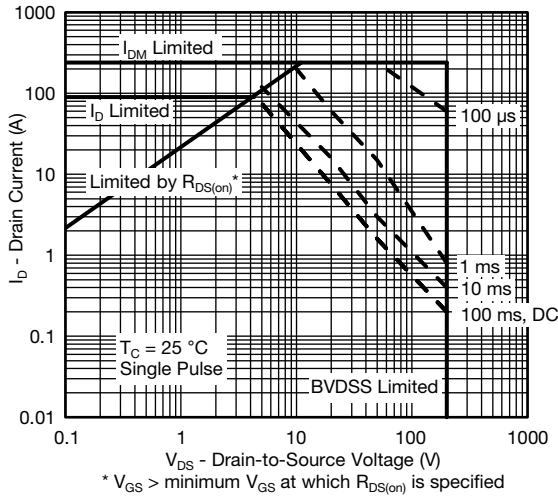


**Source Drain Diode Forward Voltage**

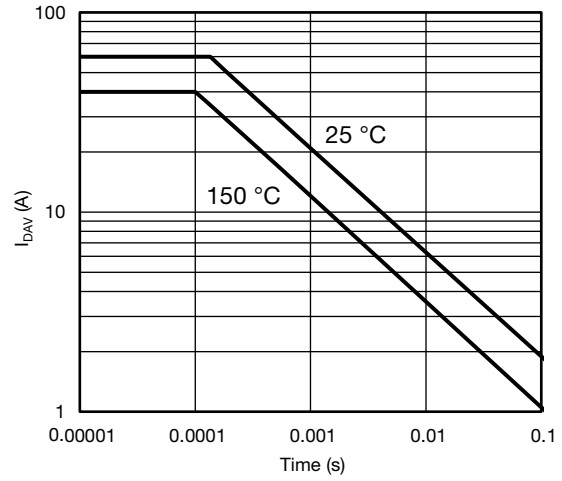


**Current De-rating**

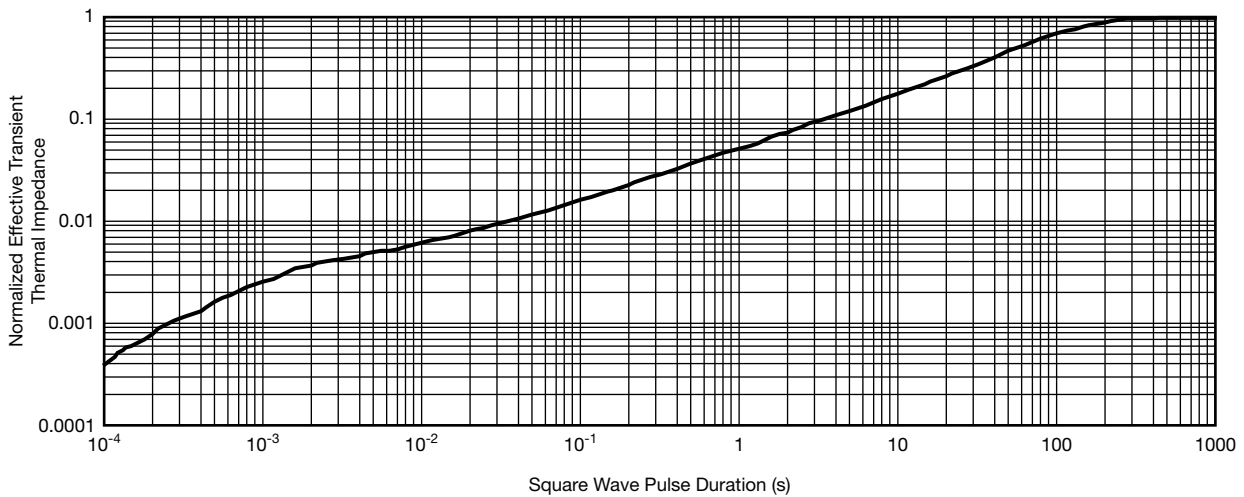
**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Safe Operating Area**

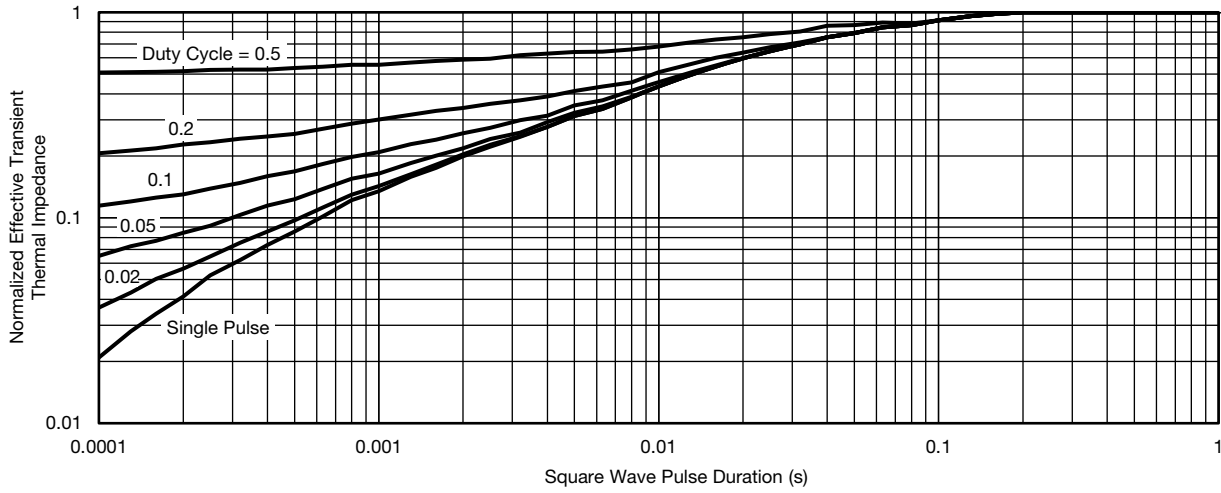


**Single Pulse Avalanche Current Capability vs. Time**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

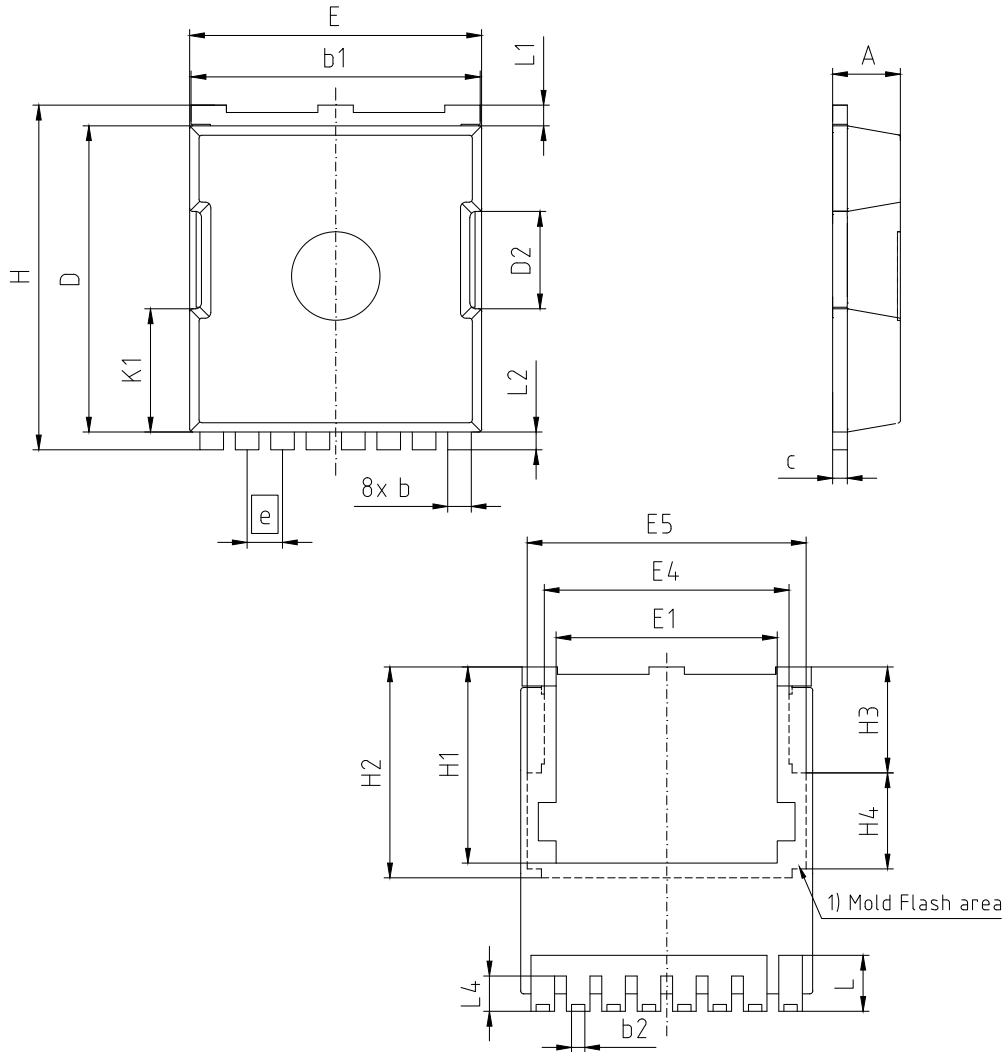


**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
    - Normalized Transient Thermal Impedance Junction to Case (25 °C)
- are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.094
b	0.70	0.90	0.028	0.035
b1	9.70	9.90	0.382	0.390
b2	0.42	0.50	0.017	0.020
c	0.40	0.60	0.016	0.024
D	10.28	10.58	0.405	0.416
D2	3.30		0.130	
E	9.70	10.10	0.382	0.398
E1	7.50		0.295	
E4	8.50		0.335	
E5	9.46		0.372	
e	1.20 (BSC)		0.047 (BSC)	
H	11.48	11.88	0.452	0.468
H1	6.55	6.75	0.258	0.266
H2	7.15		0.281	
H3	3.59		0.141	
H4	3.26		0.128	
N	8		8	
K1	4.18		0.165	
L	1.60	2.10	0.063	0.083
L1	0.70		0.028	
L2	0.60		0.024	
L4	1.00	1.30	0.039	0.051

**DOCUMENT NO.**  
Z8B00169619

**SCALE**

**EUROPEAN PROJECTION**

**ISSUE DATE**  
20-02-2014

**REVISION**  
02

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